

NTR5198NL

MOSFET – Power, Single, N-Channel, Logic Level, SOT-23

60 V, 155 mΩ



ON Semiconductor®

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Features

- Small Footprint Industry Standard Surface Mount SOT–23 Package
- Low $R_{DS(on)}$ for Low Conduction Losses and Improved Efficiency
- These Devices are Pb–Free, Halogen Free/BFR Free and are RoHS Compliant

MAXIMUM RATINGS ($T_J = 25^\circ\text{C}$ unless otherwise noted)

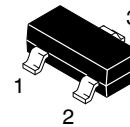
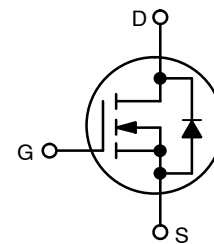
Parameter	Symbol	Value	Unit	
Drain-to-Source Voltage	V_{DSS}	60	V	
Gate-to-Source Voltage	V_{GS}	± 20	V	
Continuous Drain Current $R_{\Psi J-mb}$ (Notes 1, 2, 3, and 4)	Steady State	$T_A = 25^\circ\text{C}$	I_D 2.2	A
		$T_A = 100^\circ\text{C}$	1.6	
Power Dissipation $R_{\Psi J-mb}$ (Notes 1 and 3)	Steady State	$T_A = 25^\circ\text{C}$	P_D 1.5	W
		$T_A = 100^\circ\text{C}$	0.6	
Continuous Drain Current $R_{\theta JA}$ (Note 1, 2, 3, and 4)	Steady State	$T_A = 25^\circ\text{C}$	I_D 1.7	A
		$T_A = 100^\circ\text{C}$	1.2	
Power Dissipation $R_{\theta JA}$ (Notes 1 and 3)	Steady State	$T_A = 25^\circ\text{C}$	P_D 0.9	W
		$T_A = 100^\circ\text{C}$	0.4	
Pulsed Drain Current	$T_A = 25^\circ\text{C}$, $t_p = 10 \mu\text{s}$	I_{DM} 27	A	
Operating Junction and Storage Temperature	T_J , T_{stg}	-55 to 150	$^\circ\text{C}$	
Source Current (Body Diode)	I_S	1.9	A	
Lead Temperature for Soldering Purposes (1/8" from case for 10 s)	T_L	260	$^\circ\text{C}$	

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

1. The entire application environment impacts the thermal resistance values shown, they are not constants and are only valid for the particular conditions noted.
2. Psi (Ψ) is used as required per JESD51–12 for packages in which substantially less than 100% of the heat flows to single case surface.
3. Surface-mounted on FR4 board using a 650 mm², 2 oz. Cu pad.
4. Maximum current for pulses as long as 1 second is higher but is dependent on pulse duration and duty cycle.

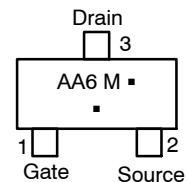
$V_{(BR)DSS}$	$R_{DS(on)}$ TYP	I_D MAX
60 V	155 mΩ @ 10 V	2.2 A
	205 mΩ @ 4.5 V	

N-Channel



SOT-23
CASE 318
STYLE 21

MARKING DIAGRAM/ PIN ASSIGNMENT



AA6 = Device Code
M = Date Code*
▪ = Pb–Free Package

(Note: Microdot may be in either location)

*Date Code orientation may vary depending upon manufacturing location.

ORDERING INFORMATION

Device	Package	Shipping†
NTR5198NLT1G	SOT–23 (Pb–Free)	3000 / Tape & Reel
NTR5198NLT3G	SOT–23 (Pb–Free)	10000 / Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specification Brochure, BRD8011/D.

NTR5198NL

THERMAL RESISTANCE RATINGS

Parameter	Symbol	Max	Unit
Junction-to-Lead #3 – Drain (Notes 2 and 3)	$R_{\Psi J-mb}$	86	°C/W
Junction-to-Ambient – Steady State (Note 3)	$R_{\theta JA}$	139	°C/W

ELECTRICAL CHARACTERISTICS ($T_J = 25^\circ\text{C}$ unless otherwise noted)

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
OFF CHARACTERISTICS						
Drain-to-Source Breakdown Voltage	$V_{(BR)DSS}$	$V_{GS} = 0\text{ V}, I_D = 250\ \mu\text{A}$	60			V
Drain-to-Source Breakdown Voltage Temperature Coefficient	$V_{(BR)DSS}/T_J$	Reference to 25°C , $I_D = 250\ \mu\text{A}$		70		mV/°C
Zero Gate Voltage Drain Current	I_{DSS}	$V_{GS} = 0\text{ V}, V_{DS} = 60\text{ V}$	$T_J = 25^\circ\text{C}$		1.0	μA
			$T_J = 125^\circ\text{C}$		10	
Gate-to-Source Leakage Current	I_{GSS}	$V_{DS} = 0\text{ V}, V_{GS} = \pm 20\text{ V}$			± 100	nA

ON CHARACTERISTICS (Note 5)

Gate Threshold Voltage	$V_{GS(TH)}$	$V_{GS} = V_{DS}, I_D = 250\ \mu\text{A}$	1.5		2.5	V
Threshold Temperature Coefficient	$V_{GS(TH)}/T_J$	Reference to 25°C , $I_D = 250\ \mu\text{A}$		-6.5		mV/°C
Drain-to-Source On-Resistance	$R_{DS(on)}$	$V_{GS} = 10\text{ V}, I_D = 1\text{ A}$		107	155	m Ω
		$V_{GS} = 4.5\text{ V}, I_D = 1\text{ A}$		142	205	
Forward Transconductance	g_{FS}	$V_{DS} = 5.0\text{ V}, I_D = 1\text{ A}$		3		S

CHARGES, CAPACITANCES & GATE RESISTANCE

Input Capacitance	C_{iss}	$V_{GS} = 0\text{ V}, f = 1.0\text{ MHz}, V_{DS} = 25\text{ V}$		182		pF
Output Capacitance	C_{oss}			25		
Reverse Transfer Capacitance	C_{rss}			16		
Total Gate Charge	$Q_G(TOT)$	$V_{DS} = 48\text{ V}, I_D = 1\text{ A}$	$V_{GS} = 4.5\text{ V}$		2.8	nC
			$V_{GS} = 10\text{ V}$		5.1	
Threshold Gate Charge	$Q_G(TH)$	$V_{DS} = 48\text{ V}, I_D = 1\text{ A}, V_{GS} = 10\text{ V}$			0.3	V
Gate-to-Source Charge	Q_{GS}				0.8	
Gate-to-Drain Charge	Q_{GD}				1.5	
Plateau Voltage	V_{GP}				3.1	
Gate Resistance	R_G				8	

SWITCHING CHARACTERISTICS (Note 6)

Turn-On Delay Time	$t_{d(on)}$	$V_{DS} = 30\text{ V}, V_{GS} = 10\text{ V}, I_D = 1\text{ A}, R_G = 10\ \Omega$		5		ns
Rise Time	t_r			7		
Turn-Off Delay Time	$t_{d(off)}$			13		
Fall Time	t_f			2		

DRAIN-SOURCE DIODE CHARACTERISTICS

Forward Diode Voltage	V_{SD}	$V_{GS} = 0\text{ V}, I_S = 1\text{ A}$	$T_J = 25^\circ\text{C}$		0.8	1.2	V
			$T_J = 125^\circ\text{C}$		0.6		
Reverse Recovery Time	t_{rr}	$I_S = 1\text{ A}_{dc}, V_{GS} = 0\text{ V}_{dc}, dI_S/dt = 100\text{ A}/\mu\text{s}$			12		ns
Charge Time	t_a				9		
Discharge Time	t_b				3		
Reverse Recovery Stored Charge	Q_{RR}				6		

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

5. Pulse Test: Pulse Width $\leq 300\ \mu\text{s}$, Duty Cycle $\leq 2\%$.

6. Switching characteristics are independent of operating junction temperatures.

TYPICAL CHARACTERISTICS

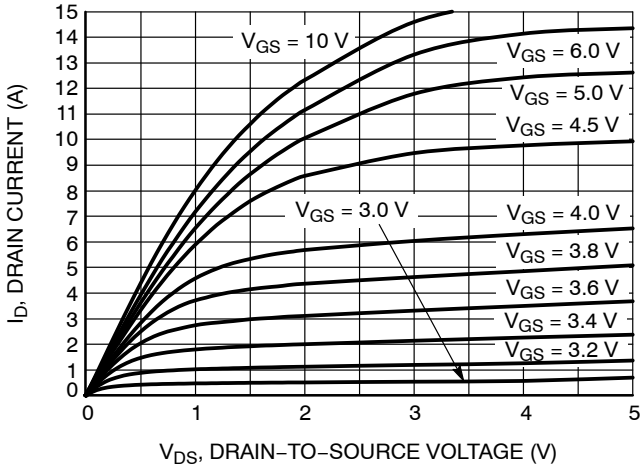


Figure 1. On-Region Characteristics

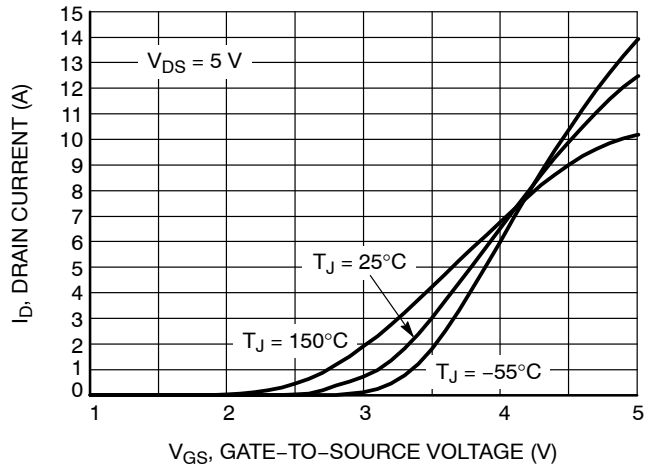


Figure 2. Transfer Characteristics

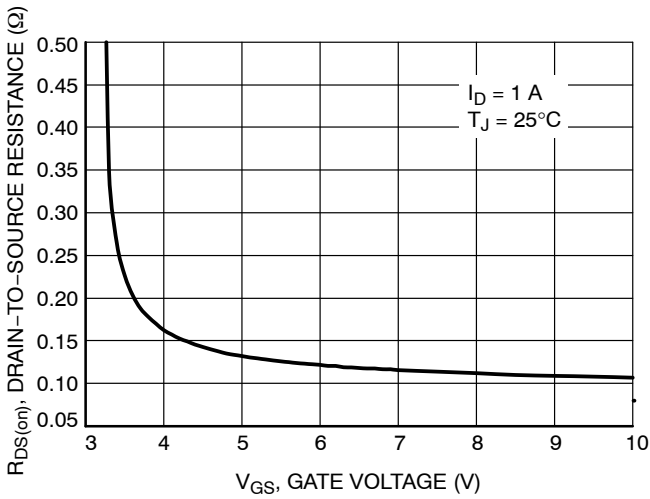


Figure 3. On-Resistance vs. Gate-to-Source Voltage

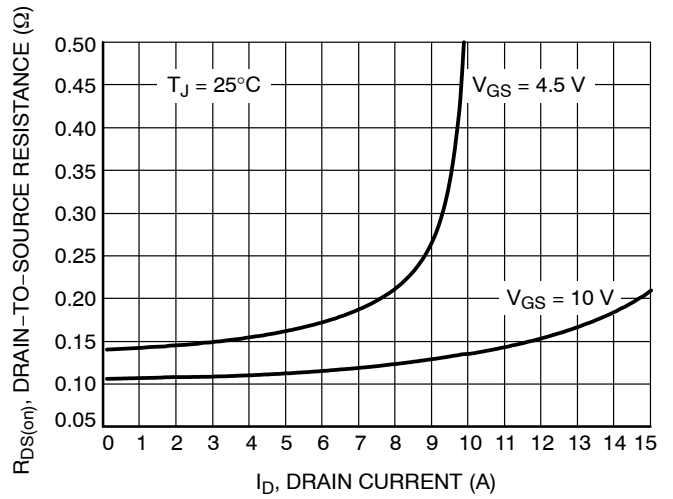


Figure 4. On-Resistance vs. Drain Current and Gate Voltage

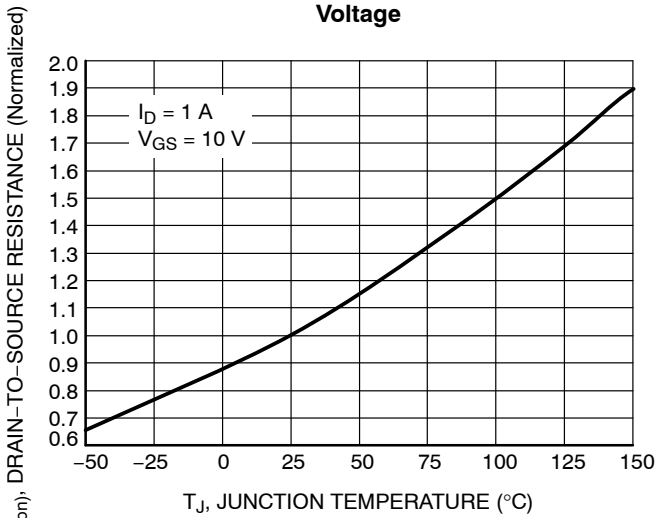


Figure 5. On-Resistance Variation with Temperature

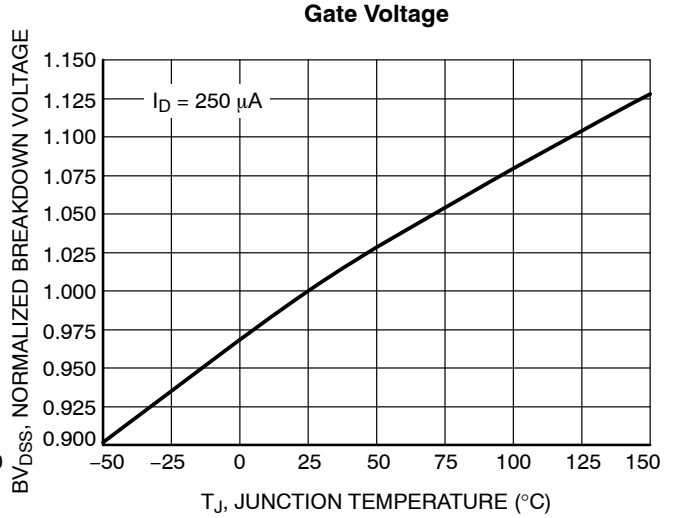


Figure 6. Breakdown Voltage Variation with Temperature

TYPICAL CHARACTERISTICS

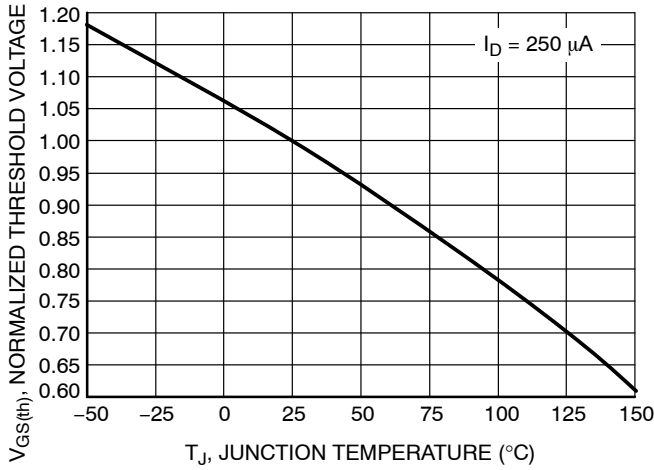


Figure 7. Threshold Voltage Variation with Temperature

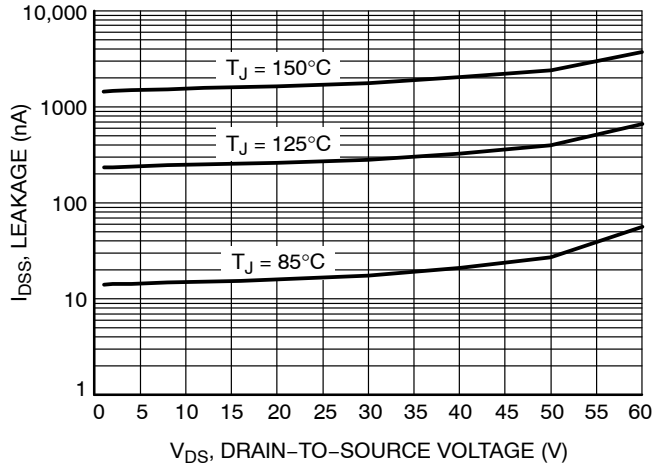


Figure 8. Drain-to-Source Leakage Current vs. Voltage

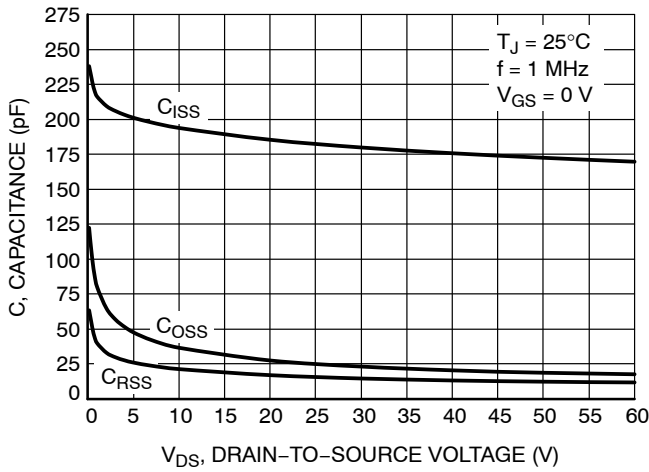


Figure 9. Capacitance Variation

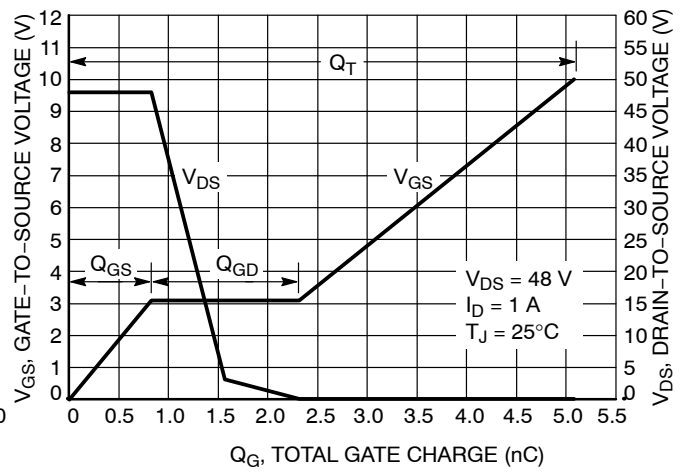


Figure 10. Gate-to-Source and Drain-to-Source Voltage vs. Total Charge

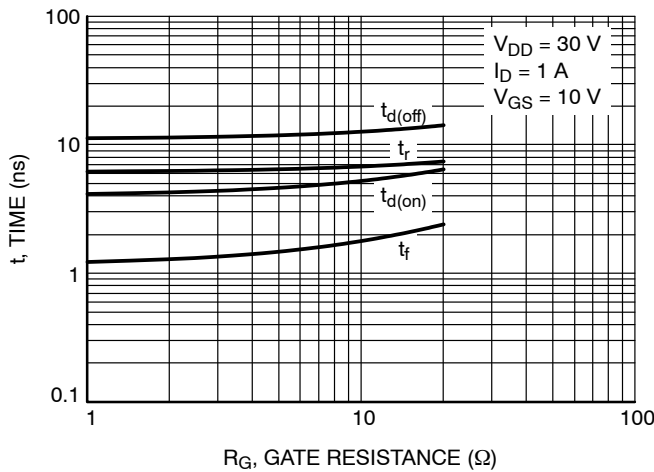


Figure 11. Resistive Switching Time Variation vs. Gate Resistance

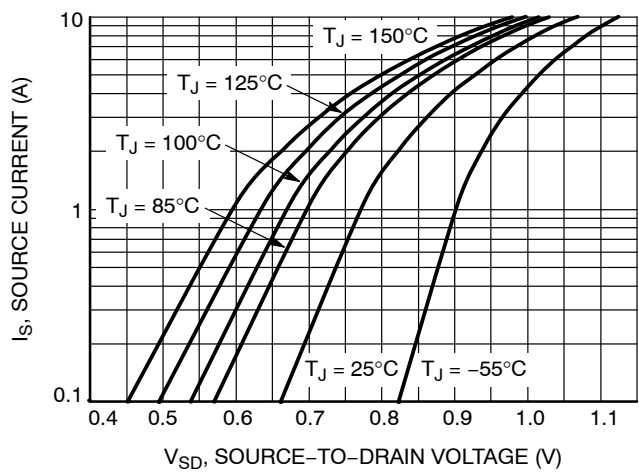


Figure 12. Diode Forward Voltage vs. Current

TYPICAL CHARACTERISTICS

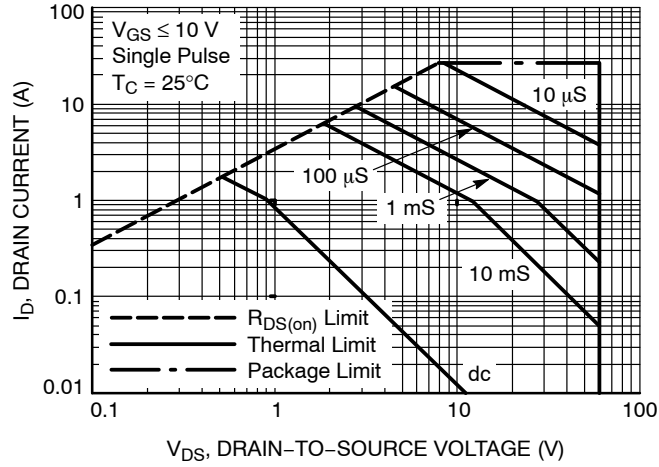


Figure 13. Maximum Rated Forward Biased Safe Operating Area

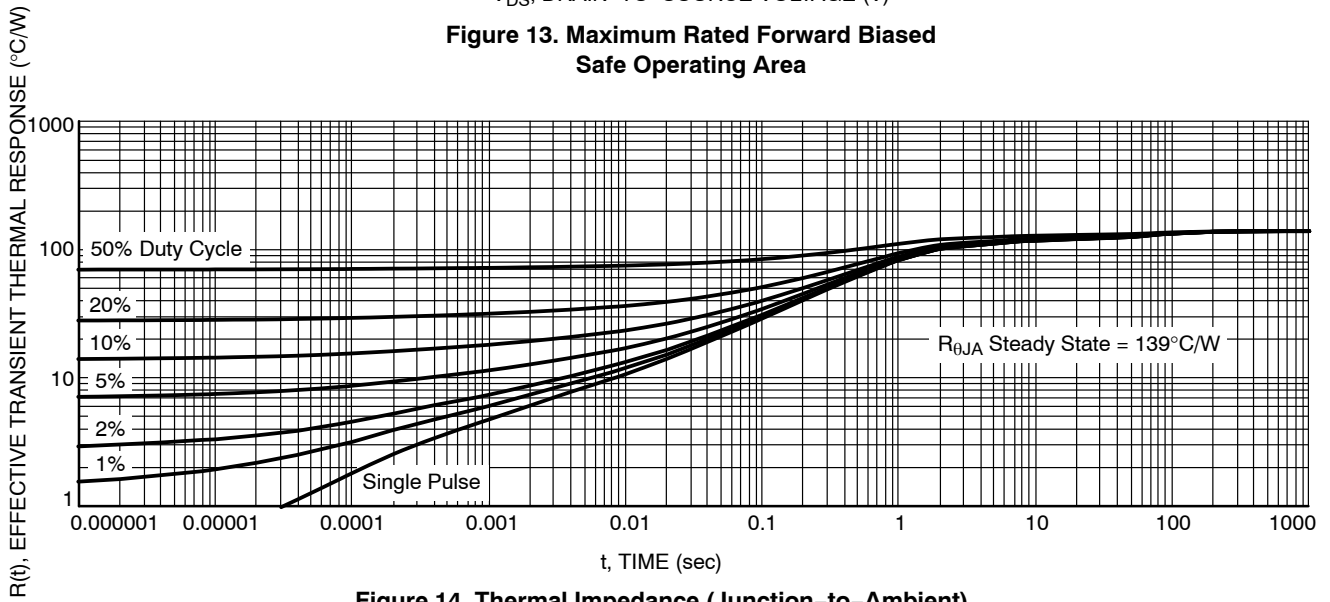


Figure 14. Thermal Impedance (Junction-to-Ambient)

MECHANICAL CASE OUTLINE

PACKAGE DIMENSIONS

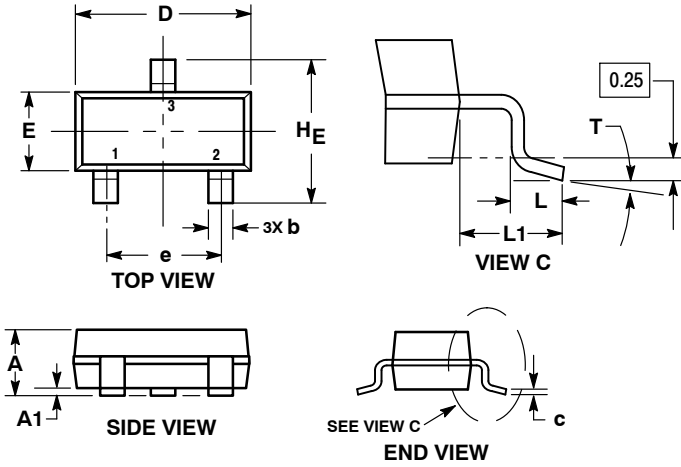
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SOT-23 (TO-236) CASE 318-08 ISSUE AS

DATE 30 JAN 2018

SCALE 4:1



NOTES:

1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
2. CONTROLLING DIMENSION: MILLIMETERS.
3. MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF THE BASE MATERIAL.
4. DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH, PROTRUSIONS, OR GATE BURRS.

DIM	MILLIMETERS			INCHES		
	MIN	NOM	MAX	MIN	NOM	MAX
A	0.89	1.00	1.11	0.035	0.039	0.044
A1	0.01	0.06	0.10	0.000	0.002	0.004
b	0.37	0.44	0.50	0.015	0.017	0.020
c	0.08	0.14	0.20	0.003	0.006	0.008
D	2.80	2.90	3.04	0.110	0.114	0.120
E	1.20	1.30	1.40	0.047	0.051	0.055
e	1.78	1.90	2.04	0.070	0.075	0.080
L	0.30	0.43	0.55	0.012	0.017	0.022
L1	0.35	0.54	0.69	0.014	0.021	0.027
HE	2.10	2.40	2.64	0.083	0.094	0.104
T	0°	---	10°	0°	---	10°

RECOMMENDED SOLDERING FOOTPRINT



GENERIC MARKING DIAGRAM*



XXX = Specific Device Code
M = Date Code
▪ = Pb-Free Package

*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "▪", may or may not be present.

STYLE 1 THRU 5:
CANCELLED

STYLE 6:
PIN 1. BASE
2. EMITTER
3. COLLECTOR

STYLE 7:
PIN 1. EMITTER
2. BASE
3. COLLECTOR

STYLE 8:
PIN 1. ANODE
2. NO CONNECTION
3. CATHODE

STYLE 9:
PIN 1. ANODE
2. ANODE
3. CATHODE

STYLE 10:
PIN 1. DRAIN
2. SOURCE
3. GATE

STYLE 11:
PIN 1. ANODE
2. CATHODE
3. CATHODE-ANODE

STYLE 12:
PIN 1. CATHODE
2. CATHODE
3. ANODE

STYLE 13:
PIN 1. SOURCE
2. DRAIN
3. GATE

STYLE 14:
PIN 1. CATHODE
2. GATE
3. ANODE

STYLE 15:
PIN 1. GATE
2. CATHODE
3. ANODE

STYLE 16:
PIN 1. ANODE
2. CATHODE
3. CATHODE

STYLE 17:
PIN 1. NO CONNECTION
2. ANODE
3. CATHODE

STYLE 18:
PIN 1. NO CONNECTION
2. CATHODE
3. ANODE

STYLE 19:
PIN 1. CATHODE
2. ANODE
3. CATHODE-ANODE

STYLE 20:
PIN 1. CATHODE
2. ANODE
3. GATE

STYLE 21:
PIN 1. GATE
2. SOURCE
3. DRAIN

STYLE 22:
PIN 1. RETURN
2. OUTPUT
3. INPUT

STYLE 23:
PIN 1. ANODE
2. ANODE
3. CATHODE

STYLE 24:
PIN 1. GATE
2. DRAIN
3. SOURCE

STYLE 25:
PIN 1. ANODE
2. CATHODE
3. GATE

STYLE 26:
PIN 1. CATHODE
2. ANODE
3. NO CONNECTION

STYLE 27:
PIN 1. CATHODE
2. CATHODE
3. CATHODE

STYLE 28:
PIN 1. ANODE
2. ANODE
3. ANODE

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[SSM6P69NU,LF](#) [DMP22D4UFO-7B](#)